

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	887626	gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 11:20
S2	639571	mos\$1fet or mis\$1fet or fet or mos or pmos or nmos or field adj4 (transistor or device)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/24 14:31
S3	83577	(multiple or differen\$2 or various) adj4 thickness	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/24 14:32
S4	2741827	insulat\$4 or di\$1electric or oxide or "sio.sub."\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/24 14:43
S5	133420	gate adj5 (insulat\$4 or di\$1electric or oxide or "sio.sub."\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/25 14:16
S6	484543	high adj3 (voltage or power)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 11:25
S7	328173	low adj3 (voltage or power)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 11:25
S8	978	gate with thick with (high adj3 (voltage or power))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/24 14:46
S9	877	gate with thin with (low adj3 (voltage or power))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/24 14:47
S10	301	(gate with thick with (high adj3 (voltage or power))) and (gate with thin with (low adj3 (voltage or power)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/24 14:49

S11	300	((gate with thick with (high adj3 (voltage or power))) and (gate with thin with (low adj3 (voltage or power)))) and ((insulat\$4 or di\$1electric or oxide or "sio.sub."\$1) or ((multiple or differen\$2 or various) adj4 thickness))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 11:36
S12	1461	438/591.ccls. or 438/585.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/24 16:04
S13	1202	(438/591.ccls. or 438/585.ccls.) and (gate adj5 (insulat\$4 or di\$1electric or oxide or "sio.sub."\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/24 16:04
S14	490	((438/591.ccls. or 438/585.ccls.) and (gate adj5 (insulat\$4 or di\$1electric or oxide or "sio.sub."\$1))) and thick and thin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/24 16:05
S15	156505	hf or hydrofluoric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/24 16:17
S16	4732	hto or high adj2 temperature adj2 oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/25 14:07
S17	503341	etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/24 16:18
S18	2493898	resistance or resistant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/24 16:19
S19	4	(hf or hydrofluoric) same (hto or high adj2 temperature adj2 oxide) same etch\$3 same (resistance or resistant)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/24 16:22
S20	2524462	etch\$3.or removed	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/24 16:23

S21	182885	bhf or boe or (hf or hydrofluoric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/24 16:25
S22	101	(bhf or boe or (hf or hydrofluoric)) same (hto or high adj2 temperature adj2 oxide) same (etch\$3 or removed)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/24 16:26
S23	4732	hto or high adj2 temperature adj2 oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/25 14:08
S24	10404321	benefit or advantag\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/25 14:08
S25	140	(hto or high adj2 temperature adj2 oxide) with (benefit or advantag\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/25 14:08
S26	133420	gate adj5 (insulat\$4 or di\$1electric or oxide or "sio.sub."\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/25 14:18
S27	302	(hto or high adj2 temperature adj2 oxide) with (gate adj5 (insulat\$4 or di\$1electric or oxide or "sio.sub."\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/25 14:19
S28	228	(hto or high adj2 temperature adj2 oxide) with teos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/25 14:20
S29	25	((hto or high adj2 temperature adj2 oxide) with (gate adj5 (insulat\$4 or di\$1electric or oxide or "sio.sub."\$1))) and ((hto or high adj2 temperature adj2 oxide) with teos)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/25 14:20
S43	25095	sti or trench adj3 isolat\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 11:20

S44	148991	planar adj5 surface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 11:21
S45	2488	S43 and S44	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 11:21
S46	16982	locos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 11:22
S47	854	S45 and S46	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 11:22
S48	1215927	wiring or inter\$1connect\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 11:23
S49	541	S47 and S48	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 11:23
S50	500527	high adj3 (voltage or power)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 11:25
S51	341399	low adj3 (voltage or power)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 11:25
S52	91	S49 and S50 and S51	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 11:25
S53	324	((gate with thick with (high adj3 (voltage or power))) and (gate with thin with (low adj3 (voltage or power)))) and ((insulat\$4 or di\$1electric or oxide or "sio.sub."\$1) or ((multiple or differen\$2 or various) adj4 thickness))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 11:35

S54	96	S53 and S43	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 11:36
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